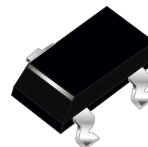


FEATURES

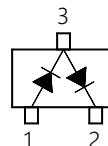
- Silicon epitaxial planar diode
- For General Purpose
- This diode is also available in other case
- Small Signal Diodes

SOT-23



MECHANICAL DATA

- Case SOT-23 plastic case
- Weight Approx. 0.01 gram



Absolute Maximum Ratings $T_a=25^{\circ}\text{C}$

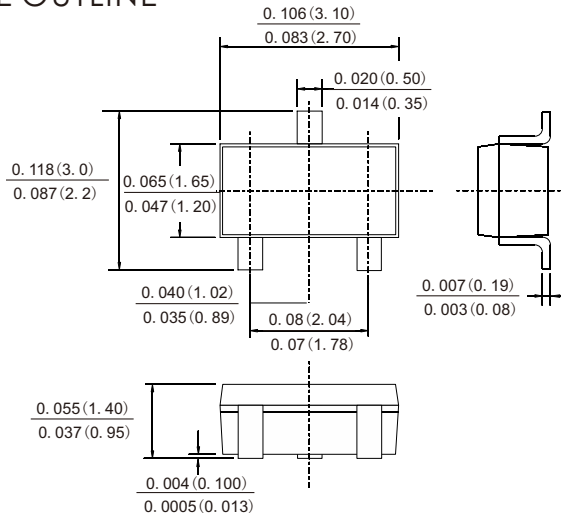
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Continuous Forward Current (Double Diode Loaded)	I_F	125	mA
Continuous Forward Current (Single Diode Loaded)	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
		1	
		4.5	
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

RATINGS AND CHARACTERISTIC CURVES BAV99

ELECTRICAL CHARACTERISTICS $T_a=25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0, f = 1 \text{ MHz}$	C_d	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}, I_R = 1 \text{ mA}, R_L = 100 \Omega$	t_{rr}	4	ns

SOT-23 PACKAGE OUTLINE



Dimensions in inches and (millimeters)